4. NOISE in RF CIRCUITS and SYSTEMS ENEL434 Electronics 2

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Summary

- Random variables (review)
- Noise basics
- Thermal noise
- Shot noise
- Flicker noise
- · Circuit noise calculations
- Equivalent noise sources and noise temperature
- Representation of a noisy 2-port
- Noise figure and noise temperature
- Noise figure of an attenuator
- Cascaded communication system
- Examples

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References

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- R E Collin, Foundations for Microwave Engineering, 2nd Edition, McGraw-Hill 1992 [Section 10.8]
- P Z Peebles, Jr, Probability, Random Variables and Random Signal Principles, 3rd Edition, McGraw-Hill 1993

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Random Variables

Consider a continuous random variable X:

- It is **possible** for X to take any value on the range: (-∞, ∞)
- The statistical behaviour is fully described by its probability density function f(x).
- The **probability** that X is within the range [a, b] is given by:

$$P(a \le X \le b) = \int_{a}^{b} f(x) dx$$

- Hence: $\int_{0}^{\infty} f(x) dx = 1$
- The mean (or loosely average value) μ_X , and variance (spread) σ_X^2 are given by:

$$\mu_X = \int\limits_{-\infty}^{\infty} x f(x) dx \qquad \sigma_X^{\ 2} = \int\limits_{-\infty}^{\infty} (x - \mu)^2 f(x) dx$$

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Random Variables

Consider two continuous random variables X and Y:

- It is **possible** for X and Y to take any value on the range: (-∞, ∞)
- The statistical behaviour of X and Y are fully described by their joint probability density function f(x,y).
- The **probability** that X is within the range [a, b] AND Y is within the range [c, d] is given by:

$$P(a \le X \le b \quad \cap \quad c \le Y \le d) = \int_{a}^{b} \int_{c}^{d} f(x,y) dy dx$$

• Hence:

$$\int_{-\infty-\infty}^{\infty}\int_{-\infty}^{\infty}f(x,y)dydx=1$$

X and Y are independent (outcome for X has no bearing on the outcome of Y) if f(x,y) = f(x)f(y)

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Random Variables

Consider two continuous random variables X and Y:

• An important statistical property is the mean of the product XY called the **correlation**:

$$R_{XY} = \int_{-\infty-\infty}^{\infty} \int_{-\infty}^{\infty} xyf(x,y)dydx$$

- If $R_{XY} = \mu_X \mu_Y$ then X and Y are uncorrelated.
- Independence of X and Y is sufficient to imply X and Y are uncorrelated. But the reverse statement is in general not true.

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Random Variables

Consider the sum of multiple independent continuous random variables

$$Y = X_1 + X_2 + ... + X_n$$

• The mean and variance of Y are:

$$\mu_{Y} = \mu_{1} + \mu_{2} + \dots + \mu_{n}$$

$$\sigma_{Y}^{2} = \sigma_{1}^{2} + \sigma_{2}^{2} + \dots + \sigma_{n}^{2}$$

where μ_k and σ_k^2 are the mean and variance respectively of X_k Central Limit Theorem: Y has a normal distribution as n tends to infinity regardless of the distributions of the components of Y $(X_1, X_2 ... X_n)$

If X₁, X₂ ... X_n all have normal distributions, then Y will have a normal distribution for any value of n

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Noise Basics

 Noise is a random low level disturbance present in all real electrical circuits.

$$v(t) = v_{Signal}(t) + n(t)$$

- Noise becomes an issue when the level of the signal is comparable to n(t).
- n(t) is a random process. That is:
 - n(t) is a random variable at time t
 - n(t₁) and n(t₂) are a pair of random variables

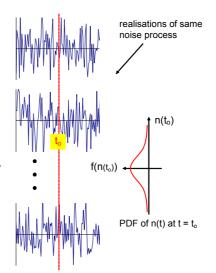


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Noise Basics

- n(t) can be characterised by a probability density function at time t.
- That is we could consider an infinite number of realisations of the same noise process.
- The mean μ_n of n(t) is zero for noise.
- The variance σ_n^2 is non-zero and is the noise power into a 1 Ω resistor (since mean is zero).
- The correlation of $n(t_1)$ and $n(t_2)$, called autocorrelation $R_{nn}(t_1,t_2)$, is of interest.
- We assume that noise is the sum of many random events. Hence, n(t) will have a normal distribution.
- Noise is called white noise if its power spectral density is constant.



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Noise Basics

- We may assume that the statistics are independent of time ie stationary. In the case of autocorrelation dependent only on time difference.
- A useful assumption is that the noise source is **ergodic**.
- This means that the statistics of n(t) can be obtained from time averages of one realisation of n(t).

$$\mu_n = \left\langle n(t) \right\rangle = 0$$

$$\langle n(t) \rangle = \lim_{T \to \infty} \frac{1}{2T} \int_{-T}^{T} n(t) dt$$

$$\sigma_n^2 = \langle (n(t) - \mu_n)^2 \rangle = \langle n(t)^2 \rangle \qquad \langle n$$

$$\sigma_n^2 = \langle (\mathbf{n}(\mathbf{t}) - \mu_n)^2 \rangle = \langle \mathbf{n}(\mathbf{t})^2 \rangle \qquad \langle n(t)^2 \rangle = \lim_{T \to \infty} \frac{1}{2T} \int_{-T}^{T} [n(t)]^2 dt$$

$$R_{nn}(t_1, t_2) = R_{nn}(\tau) = \langle n(t)n(t+\tau) \rangle$$

$$\langle n(t)n(t+\tau)\rangle = \lim_{T\to\infty} \frac{1}{2T} \int_{-T}^{T} n(t)n(t+\tau)dt$$

Noise Basics

• Another important aspect of n(t) is its power spectral density $S_{nn}(\omega)$ and may be defined so that the power into a 1Ω resistor is given by:

$$P_{nn} = \frac{1}{2\pi} \int_{-\infty}^{\infty} S_{nn}(\omega) d\omega$$

• The power into 1Ω over a small bandwidth Δf centred at $f = \omega/2\pi$:

$$dP_{nn} = 2S_{nn}(\omega)\Delta f$$

• It can be shown that

$$S_{nn}(\omega) = \int_{-\infty}^{\infty} R_{nn}(\tau) e^{-j\omega\tau} d\tau$$

- It can be shown that:
 - 1. R_{nn} is maximum at $\tau = 0$
 - 2. $\rm\,R_{nn}$ is even, so therefore, $\rm S_{nn}$ is pure real and an even function.

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Noise Basics

Say that we have two noise sources $n_1(t)$ and $n_2(t)$.

• The cross-correlation is given by:

$$R_{n_1n_2}(\tau) = \langle n_1(t)n_2(t+\tau) \rangle$$

• The cross-power spectral density is:

$$S_{n_1n_2}(\omega) = \int_{-\infty}^{\infty} R_{n_1n_2}(\tau) e^{-j\omega\tau} d\tau$$

- Unlike autocorrelation, cross-correlation is in general not even, and hence the cross-power spectral density is in general complex.
- $\mathrm{ReS}_{\mathrm{n1n2}}$ is and even function, $\mathrm{ImS}_{\mathrm{n1n2}}$ is an odd function.
- The cross-power into 1Ω over a small bandwidth Δf centred at $f = \omega/2\pi$:

$$dP_{n_1n_2} = 2Re(S_{n_1n_2}(\omega))\Delta f$$

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Thermal Noise

- In a conducting material, thermal energy manifests itself as random vibration of atoms and random motion of electrons.
- The electrons have thermal velocities significantly higher than drift velocity.
- The random motion of the electrons gives rise to a noise voltage across and noise current through the conductor.
- This noise is called thermal noise, or Johnson noise or Nyquist noise.
- Mean-square Thevenin voltage of a resistor with resistance R is:

$$\langle v_n(t)^2 \rangle = \frac{4hfBR}{e^{hf/kT} - 1}$$

where $h = 6.626 \times 10^{-34} \text{ Js}$ (Planck's constant)

 $k = 1.38 \times 10^{-23} \text{ J/K (Boltzmann's constant)}$

T is absolute temperature (K)

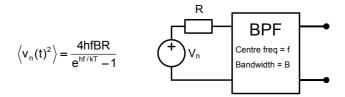
f is the centre frequency (Hz) of the system whose bandwidth is B (Hz)

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Thermal Noise

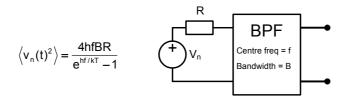


- Up to about 1000 GHz thermal noise is white: $\langle v_n(t)^2 \rangle \approx 4kTBR$
- The power spectral density of V_n is: $S_{V_nV_n}(\omega) = 2kTR$
- The noise power into bandwidth Δf is: $dP_{v_nv_n} = d \left\langle v_n(t)^2 \right\rangle = 4kTR \, \Delta f$
- A Norton equivalent is also possible.

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Thermal Noise



Because the resistor can be represented by a generator:

- Available power:
- P = kTB
- Available power spectral density: $S(\omega) = \frac{kT}{2}$

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Thermal Noise

$$\langle v_n(t)^2 \rangle = \frac{4hfBR}{e^{hf/kT} - 1} \approx 4kTBR$$

BPF

Centre freq = f

Bandwidth = B

- eg. T = 300 K, B = 100 MHz, N = 0.414 pW \equiv -93.8 dBm
- Often engineers immerse circuitry in liquid nitrogen or even liquid helium to lower T and hence noise voltage.

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Shot Noise

- Shot noise is present in semiconductor devices when conducting current.
- The current of a pn junction for example, involves the passage minority carriers across the pn junction – which are random events.
- For a junction with DC current I_o, the mean-square noise current into bandwidth B is given by:

$$\langle i_n^2 \rangle = 2qI_oB$$

where $q = 1.6 \times 10^{-19} \text{ C}$

and the power spectral density is given by: $S_{I_nI_n}(\omega) = qI_o$

- Shot noise is white.
- eg. for I $_{o}$ = 10 mA and B = 100 MHz, $\left\langle i_{n}^{~2}\right\rangle = 0.32~x10^{-12}\,A^{2}$

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Flicker or 1/f Noise

- Flicker noise is present in all semiconductor devices and resistive elements.
- Like Shot noise, Flicker noise is associated with current flow.
- Various origins but is essentially the result of contamination and defects present in manufacturing processes.
- Flicker noise is NOT white and nor is it Gaussian.
- · The power spectral density of the noise current is given by:

$$S_{l_n l_n}(\omega) = K \frac{l_o^a}{\omega^b}$$

where K, a and b are process / technology dependent constants.

a is typically in the range 0.5 to 2

b is around unity - hence "1/f" noise

 Flicker noise is negligible in microwave amplifiers but Flicker noise can be up-converted in nonlinear microwave circuits such as mixers and oscillators.

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Equivalent Noise Sources

- More often in microwave and RF engineering we are interested in the level of noise and not its physical origin.
- In this case, we would represent the noise source by an equivalent thermal noise source.
- eg. Suppose that the available noise power from an antenna is 0.1pW into a bandwidth of 100 MHz.

The available noise power N from a resistor at temperature T_e is:

$$N = kT_eB$$

Hence to achieve N = 0.1 pW into B = 100 MHz, T_e needs to be 72 K.

ie. taking a resistor and cooling it to -201°C would achieve the same noise power.

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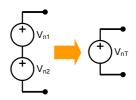
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Circuit Noise Calculations

eg. Calculate the equivalent noise voltage of two noise voltages in in series.

From a time-domain point of view ...

$$\begin{split} \left\langle v_{nT}(t)^{2}\right\rangle &= \left\langle \left(v_{n1}(t)+v_{n2}(t)\right)^{2}\right\rangle \\ &= \left\langle v_{n1}^{2}+v_{n2}^{2}+2v_{n1}v_{n2}\right\rangle \\ &= \left\langle v_{n1}^{2}\right\rangle + \left\langle v_{n2}^{2}\right\rangle + 2\left\langle v_{n1}v_{n2}\right\rangle \\ \end{split}$$
 where
$$\left\langle v_{n1}v_{n2}\right\rangle = \lim_{T\to\infty}\frac{1}{2T}\int_{T}^{T}v_{n1}(t)v_{n2}(t)dt$$



T→∞ 2T Time 2

 $\langle v_{n1}v_{n2}\rangle = 0$ for independent noise sources. Why?

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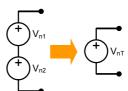
Circuit Noise Calculations

eg. Calculate the equivalent noise voltage of two noise voltages in in series.

From a **spectral domain** point of view ...

$$V_{nT} = V_{n1} + V_{n2}$$

$$\left|V_{nT}\right|^{2} = \left|V_{n1} + V_{n2}\right|^{2} = \left|V_{n1}\right|^{2} + \left|V_{n2}\right|^{2} + 2Re\left[V_{n1}V_{n2}^{\bullet}\right]$$



For deterministic signals into 1 Ω :

- $|V_{nT}|^2$ is the power of source V_{nT}
- $|V_{n1}|^2$ is the power of source V_{n1}
- $|V_{n2}|^2$ is the power of source V_{n2}
- Re(V_{n1}V_{n2}*) is a "cross-power"

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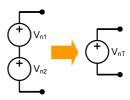
Circuit Noise Calculations

eg. Calculate the equivalent noise voltage of two noise voltages in in series.

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$$\left|V_{nT}\right|^2 = \left|V_{n1} + V_{n2}\right|^2 = \left|V_{n1}\right|^2 + \left|V_{n2}\right|^2 + 2Re\left[V_{n1}V_{n2}^{\bullet}\right]$$



For noise signals into 1 Ω over bandwidth Δf :

$$2S_{V_{nT}V_{nT}}\Delta f$$
 is the power from source V_{nT}

$$2S_{V_{n1}V_{n1}}\Delta f$$
 is the power from source V_{n1}

$$2S_{V_{n2}V_{n2}}\Delta f$$
 is the power from source V_{n2}

$$2\text{Re}(S_{V_{n1}V_{n2}})\Delta f$$
 is the cross-power from sources V_{n1} and V_{n2} noting that $\text{Re}(S_{V_{n1}V_{n2}}(-\omega)) = \text{Re}(S_{V_{n1}V_{n2}}(\omega))$

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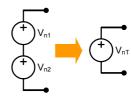
Circuit Noise Calculations

eg. Calculate the equivalent noise voltage of two noise voltages in in series.

From a spectral domain point of view ...

$$|V_{nT}|^2 = |V_{n1} + V_{n2}|^2 = |V_{n1}|^2 + |V_{n2}|^2 + 2Re[V_{n1}V_{n2}^{\bullet}]$$





$$2S_{V_{nT}V_{nT}}\Delta f = 2S_{V_{n1}V_{n1}}\Delta f + 2S_{V_{n2}V_{n2}}\Delta f + 4Re(S_{V_{n1}V_{n2}})\Delta f$$

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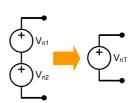
Circuit Noise Calculations

eg. Calculate the equivalent noise voltage of two noise voltages in in series.

From a spectral domain point of view ...

 V_{n1} and V_{n2} can be described by their:

- auto-correlations ↔ power spectral densities
- cross-correlation ↔ cross power spectral density



$$2S_{\vee_{nT}\vee_{nT}}\Delta f = 2S_{\vee_{n1}\vee_{n1}}\Delta f + 2S_{\vee_{n2}\vee_{n2}}\Delta f + 4\,\text{Re}\!\left(\!S_{\vee_{n1}\vee_{n2}}\right)\!\!\Delta f$$

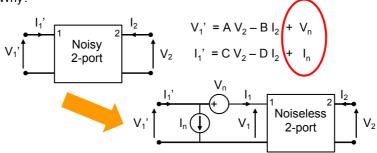
$$R_{v_{n1}v_{n2}} = \left\langle v_{n1}(t)v_{n2}(t+\tau) \right\rangle \\ S_{v_{n1}v_{n2}}(\omega) = \int\limits_{-\infty}^{\infty} R_{v_{n1}v_{n2}}(\tau)e^{-j\omega\tau}d\tau$$

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Representation of a Noisy 2-Port

- The 2-port could be a transistor, an amplifier, a coaxial cable etc.
- Due to the physical processes inherent in the 2-port, the 2-port will be noisy.
- We know that from circuit analysis that the terminal behaviour of a 2-port can be described by ABCD parameters in the frequency (spectral) domain.
- We include two noise sources at the input. These sources are correlated. Why?



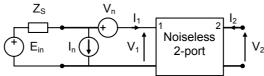
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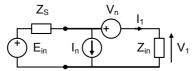
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Representation of a Noisy 2-Port

- We would normally connect a generator (Thevenin voltage $\rm E_{in}$ and impedance $\rm Z_S$) to the input of the noisy-two port.
- The generator supplies the input signal and input noise (effectively due to ReZ_S).



· Let us consider the input part of the circuit:



where Z_{in} is the input impedance to the 2-port and will be a function of load connected to port 2.

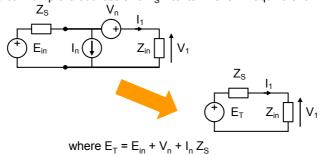
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Representation of a Noisy 2-Port

Let us analyse the input part of the circuit.

- We can arbitrarily change the polarity of V_n.
- We can lump the sources and Z_s into its Thevenin equivalent:



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Representation of a Noisy 2-Port

• The power available from the equivalent generator is:

$$E_{T} = E_{in} + V_{n} + I_{n}Z_{S}$$

$$+ E_{T} Z_{in} V_{1}$$

$$P_{A} = \frac{|E_{T}|^{2}}{4ReZ_{S}}$$

• The square of $|E_T|$ is:

$$|E_{T}|^{2} = |E_{in} + V_{n} + I_{n}Z_{S}|^{2} = |E_{in}|^{2} + |V_{n}|^{2} + |I_{n}|^{2}|Z_{S}|^{2} + 2Re[E_{in}(V_{n} + I_{n}Z_{S})^{*}] + 2Re[V_{n}(I_{n}Z_{S})^{*}]$$

$$2S_{E_{T}E_{T}}\Delta f = 2S_{E_{In}E_{In}}\Delta f + 2S_{V_{n}V_{n}}\Delta f + 2|Z_{S}|^{2}S_{I_{n}I_{n}}\Delta f$$

$$+ 4Re(S_{E_{In}V_{n}})\Delta f + 4Re(S_{E_{In}I_{n}}Z_{S}^{\bullet})\Delta f + 4Re(S_{V_{n}I_{n}}Z_{S}^{\bullet})\Delta f$$

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Representation of a Noisy 2-Port

• Note that above we use the result that:

$$\operatorname{Re}\left(S_{V_{nln}}(-\omega)Z_{s}^{*}(-\omega)\right) = \operatorname{Re}\left(S_{V_{nln}}^{*}(\omega)Z_{s}(\omega)\right) = \operatorname{Re}\left(S_{V_{nln}}(\omega)Z_{s}^{*}(\omega)\right)$$

as well as the other properties of power spectral density functions.

E_{in} is uncorrelated with V_n and I_n

$$\begin{split} 2S_{E_{T}E_{T}}\Delta f &= 2S_{E_{in}E_{in}}\Delta f + 2S_{V_{n}V_{n}}\Delta f + 2\big|Z_{S}\big|^{2}S_{I_{n}I_{n}}\Delta f \\ &+ 4Re\big(S_{E_{in}V_{n}}\big)\Delta f + 4Re\big(S_{E_{in}I_{n}}Z_{S}^{\bullet}\big)\Delta f + 4Re\big(S_{V_{n}I_{n}}Z_{S}^{\bullet}\big)\Delta f \end{split}$$



$$\begin{split} 2S_{E_{T}E_{T}}\Delta f &= 2S_{E_{In}E_{In}}\Delta f + 2S_{V_{n}V_{n}}\Delta f + 2\left|Z_{S}\right|^{2}S_{I_{n}I_{n}}\Delta f \\ &+ 4\operatorname{Re}\left(S_{V_{n}I_{n}}\right)\operatorname{Re}\left(Z_{S}\right)\Delta f + 4\operatorname{Im}\left(S_{V_{n}I_{n}}\right)\operatorname{Im}\left(Z_{S}\right)\Delta f \end{split}$$

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Representation of a Noisy 2-Port

· Finally:

$$\begin{split} 2S_{E_{T}E_{T}}\Delta f &= 2S_{E_{In}E_{In}}\Delta f + 2S_{V_{n}V_{n}}\Delta f + 2\left|Z_{S}\right|^{2}S_{I_{n}I_{n}}\Delta f \\ &+ 4\operatorname{Re}\left(S_{V_{n}I_{n}}\right)\operatorname{Re}\left(Z_{S}\right)\Delta f + 4\operatorname{Im}\left(S_{V_{n}I_{n}}\right)\operatorname{Im}\left(Z_{S}\right)\Delta f \end{split}$$



$$2S_{E_{T}E_{T}}\Delta f = 2\Delta f \left[S_{E_{in}E_{in}} + a + b|Z_{S}|^{2} + c Re Z_{S} + d Im Z_{S}\right]$$

where a, b, c and c are real constants related to the noise properties of the 2-port network

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Noise Figure and Noise Temperature

- Noise figure (F) is a figure of merit of a 2-port element (such as an amplifier or down-converter).
- The signal to noise ratio always deteriorates through its passage of linear processes.
- F measures this deterioration of SNR:

$$F = \frac{SNR_{input}}{SNR_{output}}$$

- A low F is better than a high F. The best F we could ever obtain is 1.
- We normally talk about available powers:
 - S_{input} is the signal power available from the input generator
 - S_{output} is the signal power available at the output of the 2-port
 - N_{input} is the noise power available from the generator
 - N_{output} is the noise power available at the output of the 2-port

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Noise Figure and Noise Temperature

- The 2-port will amplify (or attenuate) the input signal and noise.
- The 2-port will contribute noise.
- We can refer this contributed noise to the input of the 2-port so that it is amplified (or attenuated) by the 2-port.
- S_{output} = G_A S_{input}

where G_A is the available power gain of the 2-port

• $N_{output} = G_A N_{input} + G_A N_{added}$

where N_{added} is the noise added by the 2-port REFERED to its input

• Hence

$$\mathsf{F} \; = \; \frac{\mathsf{N}_{\mathsf{input}} \, + \mathsf{N}_{\mathsf{added}}}{\mathsf{N}_{\mathsf{input}}} \; = \; 1 + \frac{\mathsf{N}_{\mathsf{added}}}{\mathsf{N}_{\mathsf{input}}}$$

• nb. F is a power ratio so $F_{dB} = 10log_{10}F$

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Noise Figure and Noise Temperature

- Earlier we talked about equivalent noise source as though the origin of all noise is thermal.
- ie N = kTB where T is the effective noise temperature.
- $N_{input} = kT_SB$ where T_S is the effective noise temperature of the generator.
- $N_{added} = kT_eB$ where T_e is the effective noise temperature of the 2-port referred to its input port.
- Hence:

$$F = 1 + \frac{N_{added}}{N_{input}} = 1 + \frac{T_e}{T_S}$$

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Noise Figure and Noise Temperature

$$F = 1 + \frac{N_{added}}{N_{input}} = 1 + \frac{T_e}{T_S}$$

- T_e is a parameter of the 2-port. T_S is a parameter of the generator.
- Suppose we have an amplifier whose T_e is 290 K.
 - Salesman A sets T_S = 290 K and hence advertises amplifier F = 2
 - Salesman B sets T_S = 2900 K and hence advertises amplifier F = 1.1
 - Clearly Salesman B gets the most sales
 - Do you see the dilemma the customer faces when F is specified?
- For this reason whenever you calculate, write or read F it is understood that T_S = 290 K (≡ 17°C).

$$F = 1 + \frac{T_e}{290}$$

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Noise Figure and Noise Temperature

· Recall:

$$\frac{2S_{E_{T}E_{T}}\Delta f}{4ReZ_{S}} = \frac{2S_{E_{in}E_{in}}\Delta f}{4ReZ_{S}} + \frac{2\Delta f}{4ReZ_{S}} \left(a + b|Z_{S}|^{2} + cReZ_{S} + dImZ_{S}\right)$$

$$N_{total}$$

$$N_{added}$$

• Assuming that $2S_{EinEin}\Delta f$ is effectively thermal due to ReZ_S with effective temperature T_S (= 290):

$$\frac{2S_{E_{T}E_{T}}\Delta f}{4ReZ_{S}} = \frac{2\Delta f(2k \times 290 \times ReZ_{S})}{4ReZ_{S}} + \frac{2\Delta f}{4ReZ_{S}}(a + b|Z_{S}|^{2} + cReZ_{S} + dImZ_{S})$$

$$N_{total}$$

$$N_{added}$$

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Noise Figure and Noise Temperature

Hence:

$$F = \frac{N_{input} + N_{added}}{N_{input}} = 1 + \frac{\alpha |Z_S|^2 + \beta Re Z_S + \gamma Im Z_S + \epsilon}{Re Z_S}$$

where α , β , γ and ϵ are real constants related to the noise properties of the 2-port network

With some algebraic manipulation:

$$F = F_{min} + G_m \frac{\left| Z_S - Z_{opt} \right|^2}{Re Z_S}$$

where F_{min} is the minimum noise figure

 $\boldsymbol{Z}_{\text{opt}}$ is the generator impedance that minimises $\boldsymbol{F},$ and

G_m is a proportionality constant with dimensions conductance.

• nb. G_m is not a physical conductance

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Noise Figure and Noise Temperature

But:

$$\Gamma_{S} = \frac{Z_{S} - Z_{o}}{Z_{S} + Z_{o}} \qquad \quad \Gamma_{opt} = \frac{Z_{opt} - Z_{o}}{Z_{opt} + Z_{o}}$$

where Z_o is the reference impedance for reflection coefficient and Sparameters. Substitution into:

$$F = F_{min} + G_{m} \frac{\left| Z_{S} - Z_{opt} \right|^{2}}{Re Z_{S}}$$

yields:

$$F = F_{min} + G_{m} \frac{|Z_{S} - Z_{opt}|^{2}}{Re Z_{S}}$$

$$F = F_{min} + \frac{4R_{n}}{Z_{o}} \frac{|\Gamma_{S} - \Gamma_{opt}|^{2}}{(1 - |\Gamma_{S}|^{2})|1 + \Gamma_{opt}|^{2}}$$

where F_{min} is the minimum noise figure

 Γ_{opt} is the value of Γ_S that minimises F, and

R_n is a proportionality constant called the "noise resistance" and is NOT a physical resistance.

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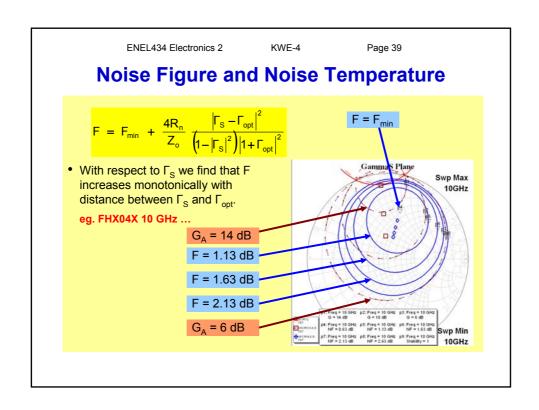
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Noise Figure and Noise Temperature

$$F = F_{min} + \frac{4R_{n}}{Z_{o}} \frac{|\Gamma_{S} - \Gamma_{opt}|^{2}}{(1 - |\Gamma_{S}|^{2})|1 + \Gamma_{opt}|^{2}}$$

- The above expressions tell us how F varies with choice of $\Gamma_{\rm S}$
- Recall that gain is also dependent on Γ_{S}
- . This means that amplifier design requires trade-off of gain and F
- · Fortunately ultra-low noise transistors are designed so that:
 - Γ_{S} in the vicinity of Γ_{opt} is associated with high gain
 - R_n is low so that F increases at a low rate as Γ_S moves away from Γ_{opt}



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Example

Fujitsu High Electron Mobility Transistor (HEMT): FHX14X

Source: www.eudyna.com

At V_{DS} = 2 V, I_D = 10 mA, 20 GHz and ambient temperature of 25°C:

 $S_{11} = 0.523 / -140.0^{\circ}$ $S_{12} = 0.133 / 58.4^{\circ}$

 $S_{21} = 2.314 / 70.8^{\circ}$

S₂₂ = 0.335 / -59.4°

 $\frac{R_N}{Z_o}$ = 0.07 F_{min} = 1.03 dB = 1.268

What is the poise figure if simultaneous conjugate matching is used?

Based upon the S-parameters at 16 GHz, the generator and load reflection coefficients that accomplish simultaneous conjugate matching are:

 $\Gamma_{\rm I} = 0.775 / 72^{\circ}$

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Example

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$$S_{12} = 0.133 / 58.4^{\circ}$$

$$\Gamma_{\rm opt} = 0.52 / 136^{\circ}$$

$$\Gamma_{\text{opt}} = 0.52 / 136^{\circ}$$
 $\frac{R_{\text{N}}}{Z_{\circ}} = 0.07$ $F_{\text{min}} = 1.03 \text{ dB} = 1.268$

What is the noise figure if simultaneous conjugate matching is used?

With $\Gamma_S = 0.835 / 146^{\circ}$ the noise figure is:

$$F = F_{min} + \frac{4R_n}{Z_o} \frac{\left|\Gamma_S - \Gamma_{opt}\right|^2}{\left(1 - \left|\Gamma_S\right|^2\right)\left|1 + \Gamma_{opt}\right|^2} = 1.268 + 4 \times 0.07 \times \frac{\left|0.835/146^\circ - 0.52/136^\circ\right|^2}{\left(1 - 0.835^2\right)\left|1 + 0.52/136^\circ\right|^2}$$

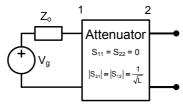
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Noise Figure of an Attenuator

Consider an attenuator with matched ports and driven by a matched generator (reference impedance Z_o is also pure real):



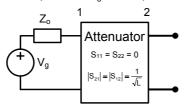
- We assume that the generator and attenuator are at temperature T.
- Hence, N_{in} = kTB
- Looking into port 2 the equivalent is a generator with Thevenin impedance $\rm Z_{\rm o}$ and we would expect it to have a noise temperature of T.
- Hence, $N_0 = kTB$

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Noise Figure of an Attenuator

Consider an attenuator with matched ports and driven by a matched generator (reference impedance Z_o is also pure real):



- But: $N_o = \frac{1}{L} (N_{in} + N_{added}) = \frac{1}{L} (kTB + N_{added})$
- Hence: $N_{added} = (L 1) kTB = kT_eB$ where $T_e = (L 1)T$

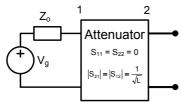
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Noise Figure of an Attenuator

Consider an attenuator with matched ports and driven by a matched generator (reference impedance $Z_{\rm o}$ is also pure real):



• Using the relationship for F (= 1 + $T_e/290$):

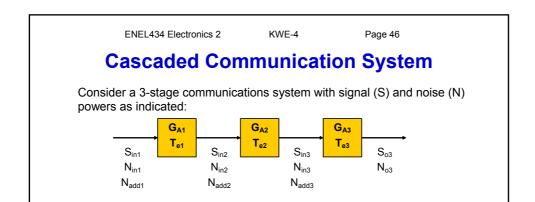
$$F = 1 + (L - 1) \frac{T}{290}$$

 This means that F is equal to its insertion loss L when it has a physical temperature of 290 K.

KWE-4 ENEL434 Electronics 2 Page 45 **Cascaded Communication System** Consider a 3-stage communications system with signal (S) and noise (N) powers as indicated: G_{A1} G_{A2} T_{e3} $\boldsymbol{T}_{\text{e1}}$ T_{e2} S_{in1} S_{o3} N_{in1} N_{in2} $N_{\text{in}3}$ N_{o3} N_{add1} N_{add2} N_{add3}

We make the assumption that over the bandwidth B:

- Thermal noise models can be used. eg:
 - $N_{in1} = kT_SB$ where T_S is the noise temperature of the input source
 - $N_{add1} = kT_{e1}B$
- T_S, T_{e1}, G_{A1} etc are flat



Considering the signal powers:

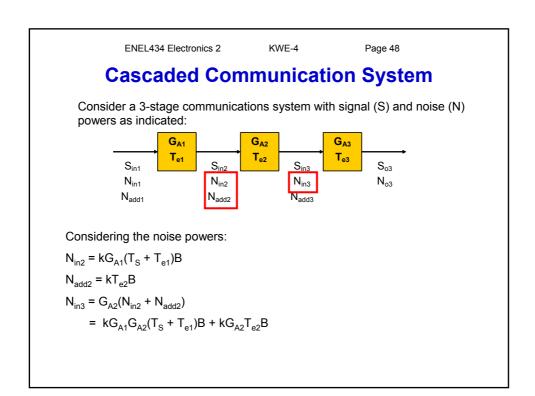
$$S_{in2} = G_{A1}S_{in1}$$

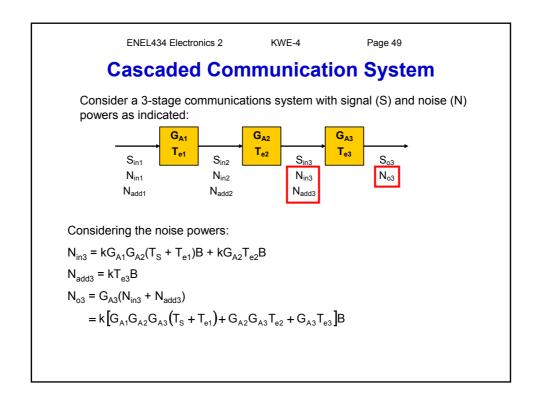
$$S_{in3} = G_{A2}S_{in2} = G_{A1}G_{A2}S_{in1}$$

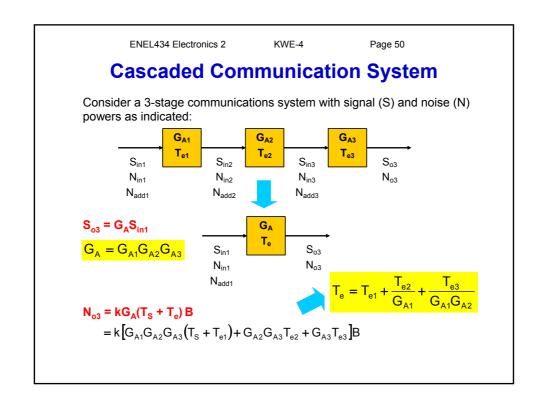
$$S_{o3} = G_{A3}S_{in3} = G_{A1}G_{A2}G_{A3}S_{in1}$$

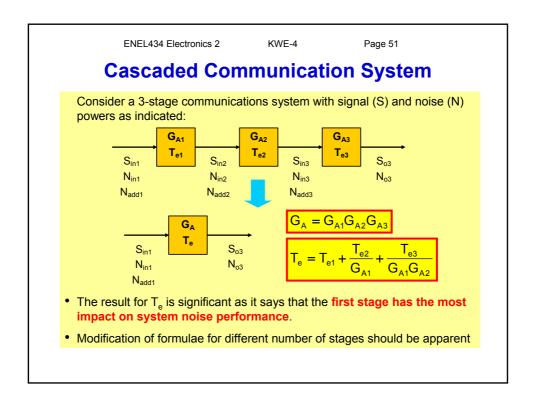
So the overall available gain is $G_A = G_{A1}G_{A2}G_{A3}$

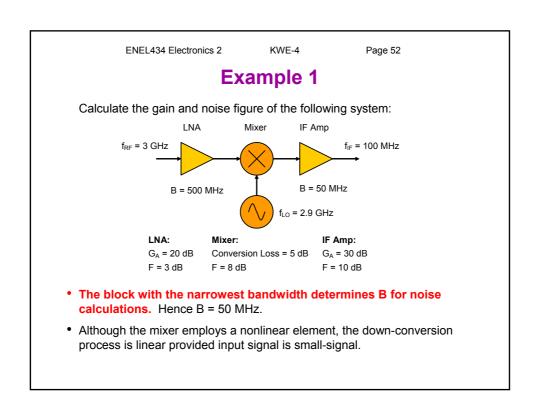
KWE-4 ENEL434 Electronics 2 Page 47 **Cascaded Communication System** Consider a 3-stage communications system with signal (S) and noise (N) powers as indicated: G_{A1} G_{A2} $\boldsymbol{T}_{\text{e1}}$ T_{e2} T_{e3} Sin S_{in3} S_{o3} N_{in1} N_{in2} N_{in3} N_{o3} N_{add3} Considering the noise powers: $N_{in1} = kT_SB$ where T_S is the noise temperature of the input source $N_{add1} = kT_{e1}B$ $N_{in2} = G_{A1}(N_{in1} + N_{add1})$ $= kG_{A1}(T_S + T_{e1})B$

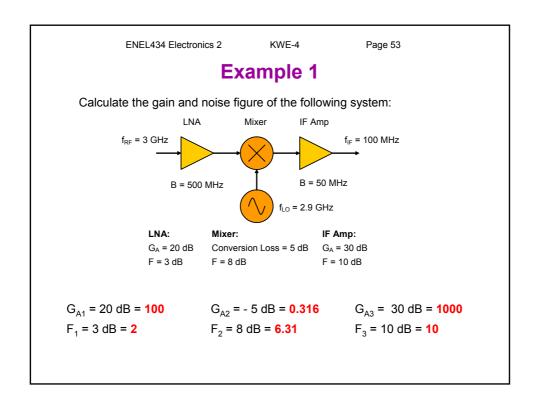












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Example 1

$$G_{A1} = 20 \text{ dB} = 100$$
 $G_{A2} = -5 \text{ dB} = 0.316$ $G_{A3} = 30 \text{ dB} = 1000$
 $F_1 = 3 \text{ dB} = 2$ $F_2 = 8 \text{ dB} = 6.31$ $F_3 = 10 \text{ dB} = 10$
 $T_{e1} = 290(2 - 1)$ $T_{e2} = 290(6.31 - 1)$ $T_{e3} = 290(10 - 1)$ $T_{e3} = 290 \text{ dB} = 100 \text{ dB} = 100$

$$G_{A} = G_{A1}G_{A2}G_{A3} = 100 \times 0.316 \times 1000$$

$$G_{A} = 31600$$

$$G_{A} = 31600$$

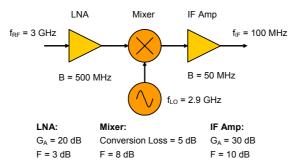
$$G_{A} = 31600$$

$$G_{A} = 31600$$

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Example 2

Calculate the minimum input signal power so that the output SNR is greater than 15 dB when the input source has a noise temperature of 100 K.



We know from the previous example:

 T_e = 388 K G_A = 31600 and B = 50 MHz

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Example 2

Output signal power:

$$S_o = G_A S_{in}$$

Output noise power:

$$N_o = k(T_e + T_S)BG_A$$

Output SNR:

$$SNR_o = \frac{G_A S_{in}}{k(T_e + T_S)BG_A}$$

Hence:

$$S_{in} = k(T_e + T_S)B SNR_o$$

= 1.38 \times 10^{-23} (388 + 100)50 \times 10^6 \times 31.6

 $= 1.064 \times 10^{-11} \text{ W}$

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Example 2

Note the input SNR:

$$SNR_{in} = \frac{S_{in}}{kT_{S}B}$$

$$= \frac{1.064 \times 10^{-11}}{1.38 \times 10^{-23} \times 100 \times 50 \times 10^{6}}$$

$$= 154$$

= 22 dB

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Example 3

You are to design a satellite TV receiver front-end low-noise block (LNB) and integrate it with the antenna which is to be located outdoors and 5 m away from the indoor unit (containing mixer, IF amp, decoder etc).

Specifications and considerations include:

- Centre frequency = 11.4 GHz
- Bandwidth = 300 MHz
- . Maximum noise figure of 4 dB
- . Minimum gain of 55 dB
- Antenna is to be located 5 m away from the indoor unit
- Indoor unit contains down-converter, IF amplifier, decoder etc.
- The box to contain outdoor electronics needs to be weather proof and its cost increases with size.

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Example 3

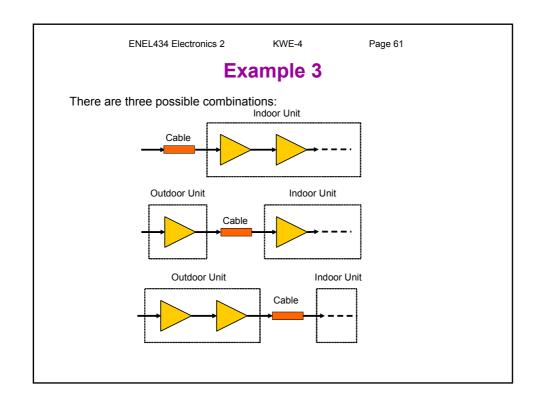
You are restricted to use the following:

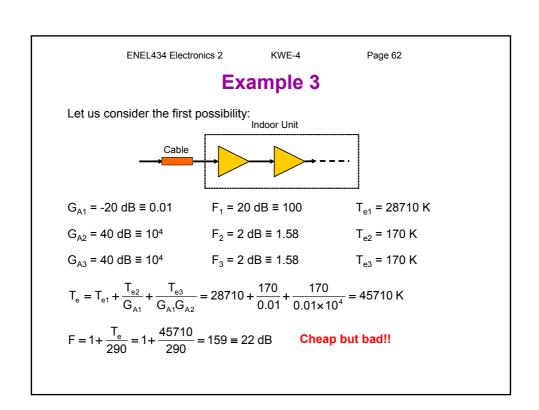
1 x Antenna: $T_e = 150 \text{ K}$

 $2 \times Amplifier: G_A = 40 dB F = 2 dB$

1 x Coaxial cable: Length = 5 m Loss = 20 dB

- The low noise bock can therefore use two amplifiers and there will be a coaxial cable connecting the antenna / outdoor unit to the indoor unit.
- The issues are whether we have electronics (amplifier(s)) outside in an outdoor unit or place them in the indoor unit.
- The overall gain of the two amplifiers and the coaxial cable is 60 dB thereby satisfying the gain specification.
- The overall gain does not depend on what order the these blocks are arranged.





KWE-4 Page 63 ENEL434 Electronics 2 Example 3 Let us consider the second possibility: Outdoor Unit Indoor Unit Cable $G_{A1} = 40 \text{ dB} \equiv 10^4$ $F_1 = 2 \text{ dB} \equiv 1.58$ $T_{e1} = 170 \text{ K}$ $G_{A2} = -20 \text{ dB} \equiv 0.01$ $F_2 = 20 \text{ dB} \equiv 100$ T_{e2} = 28710 K $G_{A3} = 40 \text{ dB} \equiv 10^4$ $F_3 = 2 dB \equiv 1.58$ $T_{e3} = 170 \text{ K}$ $T_{e} = T_{e1} + \frac{T_{e2}}{G_{A1}} + \frac{T_{e3}}{G_{A1}G_{A2}} = 170 + \frac{28710}{10^4} + \frac{170}{10^4 \times 0.01} = 175 \text{ K}$ $F = 1 + \frac{T_e}{290} = 1 + \frac{175}{290} = 1.6 \equiv 2.04 \text{ dB}$ Achieves spec at lowest cost